Ting-Chang Chang

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/4933996/publications.pdf

Version: 2024-02-01

512 papers	9,808 citations	50170 46 h-index	79541 73 g-index
516 all docs	516 docs citations	516 times ranked	5446 citing authors

#	Article	IF	Citations
1	Resistance random access memory. Materials Today, 2016, 19, 254-264.	8.3	391
2	Developments in nanocrystal memory. Materials Today, 2011, 14, 608-615.	8.3	285
3	Influence of electrode material on the resistive memory switching property of indium gallium zinc oxide thin films. Applied Physics Letters, 2010, 96, .	1.5	188
4	Behaviors of InGaZnO thin film transistor under illuminated positive gate-bias stress. Applied Physics Letters, 2010, 97, .	1.5	166
5	Influence of positive bias stress on N2O plasma improved InGaZnO thin film transistor. Applied Physics Letters, 2010, 96, .	1.5	158
6	Multilevel resistive switching in Ti/CuxO/Pt memory devices. Journal of Applied Physics, 2010, 108, .	1.1	144
7	Investigating the degradation behavior caused by charge trapping effect under DC and AC gate-bias stress for InGaZnO thin film transistor. Applied Physics Letters, 2011, 99, .	1.5	135
8	Physical and chemical mechanisms in oxide-based resistance random access memory. Nanoscale Research Letters, 2015, 10, 120.	3.1	130
9	Bias-induced oxygen adsorption in zinc tin oxide thin film transistors under dynamic stress. Applied Physics Letters, 2010, 96, .	1.5	120
10	Redox Reaction Switching Mechanism in RRAM Device With $hbox{Pt/CoSiO}_{X}hbox{/}hbox{TiN}$ Structure. IEEE Electron Device Letters, 2011, 32, 545-547.	2.2	120
11	High-Performance Visible-Blind Ultraviolet Photodetector Based on IGZO TFT Coupled with pâ€“n Heterojunction. ACS Applied Materials & Interfaces, 2018, 10, 8102-8109.	4.0	106
12	Bipolar Resistive Switching Characteristics of Transparent Indium Gallium Zinc Oxide Resistive Random Access Memory. Electrochemical and Solid-State Letters, 2010, 13, H191.	2.2	100
13	Atomic-level quantized reaction of HfO_x memristor. Applied Physics Letters, 2013, 102, 172903.	1.5	100
14	Integrated One Diodeâ€“One Resistor Architecture in Nanopillar SiO_x Resistive Switching Memory by Nanosphere Lithography. Nano Letters, 2014, 14, 813-818.	4.5	97
15	Light-induced instability of an InGaZnO thin film transistor with and without SiOx passivation layer formed by plasma-enhanced-chemical-vapor-deposition. Applied Physics Letters, 2010, 97, .	1.5	95
16	Functionally Complete Boolean Logic in 1T1R Resistive Random Access Memory. IEEE Electron Device Letters, 2017, 38, 179-182.	2.2	95
17	Demonstration of Synaptic Behaviors and Resistive Switching Characterizations by Proton Exchange Reactions in Silicon Oxide. Scientific Reports, 2016, 6, 21268.	1.6	84
18	A low-temperature method for improving the performance of sputter-deposited ZnO thin-film transistors with supercritical fluid. Applied Physics Letters, 2009, 94, .	1.5	72

#	Article	IF	Citations
19	Environment-dependent thermal instability of sol-gel derived amorphous indium-gallium-zinc-oxide thin film transistors. Applied Physics Letters, 2011, 98, 152109.	1.5	72
20	An electro-photo-sensitive synaptic transistor for edge neuromorphic visual systems. Nanoscale, 2019, 11, 17590-17599.	2.8	71
21	Effects of Ambient Atmosphere on Electrical Characteristics of Al2O3 Passivated InGaZnO Thin Film Transistors during Positive-Bias-Temperature-Stress Operation. Electrochemical and Solid-State Letters, 2011, 14, H177.	2.2	70
22	Low-power bipolar resistive switching TiN/HfO₂/ITO memory with self-compliance current phenomenon. Applied Physics Express, 2014, 7, 034101.	1.1	70
23	Enhancing the Oxygen Plasma Resistance of Low-kMethylsilsesquioxane by H2Plasma Treatment. Japanese Journal of Applied Physics, 1999, 38, 3482-3486.	0.8	65
24	Influence of H[sub 2]O Dipole on Subthreshold Swing of Amorphous Indiumâ€“Galliumâ€“Zinc-Oxide Thin Film Transistors. Electrochemical and Solid-State Letters, 2011, 14, H114.	2.2	64
25	Characteristics and Mechanisms of Silicon-Oxide-Based Resistance Random Access Memory. IEEE Electron Device Letters, 2013, 34, 399-401.	2.2	62
26	Efficient Implementation of Boolean and Full-Adder Functions With 1T1R RRAMs for Beyond Von Neumann In-Memory Computing. IEEE Transactions on Electron Devices, 2018, 65, 4659-4666.	1.6	57
27	Realization of Functional Complete Stateful Boolean Logic in Memristive Crossbar. ACS Applied Materials & Interfaces, 2016, 8, 34559-34567.	4.0	56
28	Attaining resistive switching characteristics and selector properties by varying forming polarities in a single HfO₂-based RRAM device with a vanadium electrode. Nanoscale, 2017, 9, 8586-8590.	2.8	56
29	Origin of Hopping Conduction in Graphene-Oxide-Doped Silicon Oxide Resistance Random Access Memory Devices. IEEE Electron Device Letters, 2013, 34, 677-679.	2.2	55
30	Charge Quantity Influence on Resistance Switching Characteristic During Forming Process. IEEE Electron Device Letters, 2013, 34, 502-504.	2.2	55
31	Characterization of Oxygen Accumulation in Indium-Tin-Oxide for Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 630-632.	2.2	55
32	Nonvolatile reconfigurable sequential logic in a HfO₂ resistive random access memory array. Nanoscale, 2017, 9, 6649-6657.	2.8	55
33	A Novel Nanowire Channel Poly-Si TFT Functioning as Transistor and Nonvolatile SONOS Memory. IEEE Electron Device Letters, 2007, 28, 809-811.	2.2	54
34	Conduction Mechanism and Improved Endurance in HfO2-Based RRAM with Nitridation Treatment. Nanoscale Research Letters, 2017, 12, 574.	3.1	54
35	Functional Demonstration of a Memristive Arithmetic Logic Unit (MemALU) for Inâ€Memory Computing. Advanced Functional Materials, 2019, 29, 1905660.	7.8	54
36	Reducing operation current of Ni-doped silicon oxide resistance random access memory by supercritical CO2 fluid treatment. Applied Physics Letters, 2011, 99, .	1.5	53

#	Article	IF	Citations
37	High-Density Memristor-CMOS Ternary Logic Family. IEEE Transactions on Circuits and Systems I: Regular Papers, 2021, 68, 264-274.	3.5	53
38	A study of resistive switching effects on a thin FeOx transition layer produced at the oxide/iron interface of TiN/SiO2/Fe-contented electrode structures. Applied Physics Letters, 2010, 96, 052111.	1.5	51
39	Influence of Nanocrystals on Resistive Switching Characteristic in Binary Metal Oxides Memory Devices. Electrochemical and Solid-State Letters, 2011, 14, H135.	2.2	51
40	Effects of H[sub 2] plasma treatment on low dielectric constant methylsilsesquioxane. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2325.	1.6	50
41	Bulk Oxygenâ€“Ion Storage in Indiumâ€“Tinâ€“Oxide Electrode for Improved Performance of HfO₂-Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 280-283.	2.2	50
42	Flexible low-temperature polycrystalline silicon thin-film transistors. Materials Today Advances, 2020, 5, 100040.	2.5	50
43	Strategies to Improve the Accuracy of Memristor-Based Convolutional Neural Networks. IEEE Transactions on Electron Devices, 2020, 67, 895-901.	1.6	49
44	High-performance hydrogenated amorphous-Si TFT for AMLCD and AMOLED applications. IEEE Electron Device Letters, 2005, 26, 731-733.	2.2	48
45	The Effect of Silicon Oxide Based RRAM with Tin Doping. Electrochemical and Solid-State Letters, 2012, 15, H65.	2.2	48
46	Bipolar Resistive RAM Characteristics Induced by Nickel Incorporated Into Silicon Oxide Dielectrics for IC Applications. IEEE Electron Device Letters, 2012, 33, 1696-1698.	2.2	48
47	LiSiO_X-Based Analog Memristive Synapse for Neuromorphic Computing. IEEE Electron Device Letters, 2019, 40, 542-545.	2.2	48
48	Impact of repeated uniaxial mechanical strain on p-type flexible polycrystalline thin film transistors. Applied Physics Letters, 2015, 106, .	1.5	47
49	Effect of mechanical-strain-induced defect generation on the performance of flexible amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors. Applied Physics Express, 2016, 9, 124101.	1.1	47
50	Reconfigurable Boolean Logic in Memristive Crossbar: The Principle and Implementation. IEEE Electron Device Letters, 2019, 40, 200-203.	2.2	47
51	Low operation voltage macromolecular composite memory assisted by graphene nanoflakes. Journal of Materials Chemistry C, 2013, 1, 552-559.	2.7	46
52	Adaptive Synaptic Memory via Lithium Ion Modulation in RRAM Devices. Small, 2020, 16, e2003964.	5.2	46
53	Origin of Hopping Conduction in Sn-Doped Silicon Oxide RRAM With Supercritical $hbox{CO}_{2}$ Fluid Treatment. IEEE Electron Device Letters, 2012, 33, 1693-1695.	2.2	45
54	Complementary resistive switching behavior induced by varying forming current compliance in resistance random access memory. Applied Physics Letters, 2015, 106, .	1.5	45

#	Article	IF	Citations
55	Characteristics of hafnium oxide resistance random access memory with different setting compliance current. Applied Physics Letters, 2013, 103, .	1.5	44
56	Enhancement of Brightness Uniformity by a New Voltage-Modulated Pixel Design for AMOLED Displays. IEEE Electron Device Letters, 2006, 27, 743-745.	2.2	43
57	Resistive switching characteristics of Sm2O3 thin films for nonvolatile memory applications. Solid-State Electronics, 2011, 63, 189-191.	0.8	43
58	Investigating the Drain-Bias-Induced Degradation Behavior Under Light Illumination for InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2012, 33, 1000-1002.	2.2	43
59	Hopping effect of hydrogen-doped silicon oxide insert RRAM by supercritical CO₂ fluid treatment. IEEE Electron Device Letters, 2013, 34, 617-619.	2.2	42
60	Effects of Repetitive Mechanical Bending Strain on Various Dimensions of Foldable Low Temperature Polysilicon TFTs Fabricated on Polyimide. IEEE Electron Device Letters, 2016, 37, 1010-1013.	2.2	42
61	Performance and characteristics of double layer porous silicon oxide resistance random access memory. Applied Physics Letters, 2013, 102, .	1.5	41
62	Resistance Switching Induced by Hydrogen and Oxygen in Diamond-Like Carbon Memristor. IEEE Electron Device Letters, 2014, 35, 1016-1018.	2.2	41
63	Dual Ion Effect of the Lithium Silicate Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 530-532.	2.2	41
64	Analog Resistive Switching and Synaptic Functions in WO_x/TaO_x Bilayer through Redox-Induced Trap-Controlled Conduction. ACS Applied Electronic Materials, 2019, 1, 2422-2430.	2.0	41
65	NBTI Degradation in LTPS TFTs Under Mechanical Tensile Strain. IEEE Electron Device Letters, 2011, 32, 907-909.	2.2	40
66	Investigation for coexistence of dual resistive switching characteristics in DyMn2O5 memory devices. Applied Physics Letters, 2011, 99, .	1.5	40
67	Self-Heating-Effect-Induced Degradation Behaviors in a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2013, 34, 63-65.	2.2	40
68	Endurance Improvement Technology With Nitrogen Implanted in the Interface of ${m WSiO}_{f x}$ Resistance Switching Device. IEEE Electron Device Letters, 2013, 34, 864-866.	2.2	40
69	Review of Present Reliability Challenges in Amorphous In-Ga-Zn-O Thin Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Q3058-Q3070.	0.9	40
70	Surface Engineering of Polycrystalline Silicon for Long-Term Mechanical Stress Endurance Enhancement in Flexible Low-Temperature Poly-Si Thin-Film Transistors. ACS Applied Materials & Interfaces, 2017, 9, 11942-11949.	4.0	40
71	Reliability characteristics of NiSi nanocrystals embedded in oxide and nitride layers for nonvolatile memory application. Applied Physics Letters, 2008, 92, 152114.	1.5	39
72	Silicon introduced effect on resistive switching characteristics of WOX thin films. Applied Physics Letters, 2012, 100, 022904.	1.5	39

#	Article	IF	Citations
73	Electrical conduction mechanism of Zn:SiO_x resistance random access memory with supercritical CO₂ fluid process. Applied Physics Letters, 2013, 103, 083509.	1.5	39
74	Resistive Switching Modification by Ultraviolet Illumination in Transparent Electrode Resistive Random Access Memory. IEEE Electron Device Letters, 2014, 35, 633-635.	2.2	39
75	Suppress temperature instability of InGaZnO thin film transistors by N2O plasma treatment, including thermal-induced hole trapping phenomenon under gate bias stress. Applied Physics Letters, 2012, 100, .	1.5	38
76	Effects of Varied Negative Stop Voltages on Current Self-Compliance in Indium Tin Oxide Resistance Random Access Memory. IEEE Electron Device Letters, 2015, 36, 564-566.	2.2	37
77	Low-temperature method for enhancing sputter-deposited HfO2 films with complete oxidization. Applied Physics Letters, 2007, 91, 012109.	1.5	36
78	Self-heating enhanced charge trapping effect for InGaZnO thin film transistor. Applied Physics Letters, 2012, 101, 042101.	1.5	35
79	Dehydroxyl effect of Sn-doped silicon oxide resistance random access memory with supercritical CO2 fluid treatment. Applied Physics Letters, 2012, 101, .	1.5	35
80	Improvement of resistance switching characteristics in a thin FeOx transition layer of TiN/SiO2/FeOx/FePt structure by rapid annealing. Applied Physics Letters, 2010, 96, 222108.	1.5	34
81	Bipolar resistive switching of chromium oxide for resistive random access memory. Solid-State Electronics, 2011, 62, 40-43.	0.8	34
82	Resistive switching characteristics of gallium oxide for nonvolatile memory application. Thin Solid Films, 2013, 529, 200-204.	0.8	34
83	A New Pixel Circuit Compensating for Brightness Variation in Large Size and High Resolution AMOLED Displays. Journal of Display Technology, 2007, 3, 398-403.	1.3	33
84	Temperature and frequency dependence of the ferroelectric characteristics of BaTiO3 thin films for nonvolatile memory applications. Applied Physics A: Materials Science and Processing, 2007, 89, 533-536.	1.1	33
85	Hot carrier effect on gate-induced drain leakage current in high-k/metal gate n-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2011, 99, .	1.5	33
86	Investigation statistics of bipolar multilevel memristive mechanism and characterizations in a thin FeOx transition layer of TiN/SiO2/FeOx/Fe structure. Journal of Applied Physics, 2011, 110, .	1.1	33
87	Asymmetric Carrier Conduction Mechanism by Tip Electric Field in $hbox{WSiO}_{X}$ Resistance Switching Device. IEEE Electron Device Letters, 2012, 33, 342-344.	2.2	33
88	High-performance polycrystalline silicon thin-film transistor with multiple nanowire channels and lightly doped drain structure. Applied Physics Letters, 2004, 84, 3822-3824.	1.5	32
89	The effect of high/low permittivity in bilayer HfO2/BN resistance random access memory. Applied Physics Letters, 2013, 102, .	1.5	32
90	Temperature-Dependent Instability of Bias Stress in InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2119-2124.	1.6	32

#	Article	IF	Citations
91	Dynamic conductance characteristics in HfO_x-based resistive random access memory. RSC Advances, 2017, 7, 12984-12989.	1.7	32
92	Investigation of on-current degradation behavior induced by surface hydrolysis effect under negative gate bias stress in amorphous InGaZnO thin-film transistors. Applied Physics Letters, 2014, 104, .	1.5	31
93	Galvanic Effect of Auâ€“Ag Electrodes for Conductive Bridging Resistive Switching Memory. IEEE Electron Device Letters, 2015, 36, 1321-1324.	2.2	31
94	Resistive Switching Mechanism of Oxygen-Rich Indium Tin Oxide Resistance Random Access Memory. IEEE Electron Device Letters, 2016, 37, 408-411.	2.2	31
95	High-Precision Symmetric Weight Update of Memristor by Gate Voltage Ramping Method for Convolutional Neural Network Accelerator. IEEE Electron Device Letters, 2020, 41, 353-356.	2.2	31
96	Improved memory window for Ge nanocrystals embedded in SiON layer. Applied Physics Letters, 2006, 89, 162105.	1.5	30
97	Low Temperature Improvement Method on ${m Zn{:}SiO}_{x}$ Resistive Random Access Memory Devices. IEEE Electron Device Letters, 2013, 34, 511-513.	2.2	30
98	Rational Hydrogenation for Enhanced Mobility and High Reliability on ZnO-based Thin Film Transistors: From Simulation to Experiment. ACS Applied Materials & Interfaces, 2016, 8, 5408-5415.	4.0	30
99	Influence of Oxygen Concentration on Resistance Switching Characteristics of Gallium Oxide. IEEE Electron Device Letters, 2012, 33, 1387-1389.	2.2	29
100	Hot-Carrier Effect on Amorphous In-Ga-Zn-O Thin-Film Transistors With a Via-Contact Structure. IEEE Electron Device Letters, 2013, 34, 638-640.	2.2	29
101	A Method to Reduce Forming Voltage Without Degrading Device Performance in Hafnium Oxide-Based 1T1R Resistive Random Access Memory. IEEE Journal of the Electron Devices Society, 2018, 6, 341-345.	1.2	29
102	Influence of Bias-Induced Copper Diffusion on the Resistive Switching Characteristics of a SiON Thin Film. Electrochemical and Solid-State Letters, 2011, 14, H93.	2.2	28
103	Origin of self-heating effect induced asymmetrical degradation behavior in InGaZnO thin-film transistors. Applied Physics Letters, 2012, 100, 232101.	1.5	28
104	Solution-based Î²-diketonate silver ink for direct printing of highly conductive features on a flexible substrate. Journal of Materials Chemistry C, 2013, 1, 5161.	2.7	28
105	Improving Performance by Doping Gadolinium Into the Indium-Tinâ€“Oxide Electrode in HfO₂-Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 584-587.	2.2	28
106	Investigation of channel width-dependent threshold voltage variation in a-InGaZnO thin-film transistors. Applied Physics Letters, 2014, 104, .	1.5	27
107	Hydrogen induced redox mechanism in amorphous carbon resistive random access memory. Nanoscale Research Letters, 2014, 9, 52.	3.1	27
108	Resistance Switching Characteristics Induced by O₂ Plasma Treatment of an Indium Tin Oxide Film for Use as an Insulator in Resistive Random Access Memory. ACS Applied Materials & Interfaces, 2017, 9, 3149-3155.	4.0	27

#	Article	IF	Citations
109	Enhanced electrical behavior from the galvanic effect in Ag-Cu alloy electrode conductive bridging resistive switching memory. Applied Physics Letters, 2018, 113, .	1.5	27
110	Ultra-violet light enhanced super critical fluid treatment in In-Ga-Zn-O thin film transistor. Applied Physics Letters, 2014, 104, .	1.5	26
111	The Demonstration of Increased Selectivity During Experimental Measurement in Filament-Type Vanadium Oxide-Based Selector. IEEE Transactions on Electron Devices, 2018, 65, 4622-4627.	1.6	26
112	Solution-processed amorphous Ga2O3:CdO TFT-type deep-UV photodetectors. Applied Physics Letters, 2020, 116, .	1.5	26
113	High temperature-induced abnormal suppression of sub-threshold swing and on-current degradations under hot-carrier stress in a-InGaZnO thin film transistors. Applied Physics Letters, 2013, 103, .	1.5	25
114	Improvement of Resistive Switching Characteristic in Silicon Oxide-Based RRAM Through Hydride-Oxidation on Indium Tin Oxide Electrode by Supercritical CO₂ Fluid. IEEE Electron Device Letters, 2015, 36, 558-560.	2.2	25
115	Hydrogen Diffusion and Threshold Voltage Shifts in Top-Gate Amorphous InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3123-3128.	1.6	25
116	A low temperature fabrication of HfO2 films with supercritical CO2 fluid treatment. Journal of Applied Physics, 2008, 103, .	1.1	24
117	Systematic Investigations on Self-Heating-Effect-Induced Degradation Behavior in a-InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2012, 59, 3389-3395.	1.6	24
118	Ultra-high resistive switching mechanism induced by oxygen ion accumulation on nitrogen-doped resistive random access memory. Applied Physics Letters, 2014, 105, .	1.5	24
119	Effects of Channel Width on Electrical Characteristics of Polysilicon TFTs With Multiple Nanowire Channels. IEEE Transactions on Electron Devices, 2005, 52, 2343-2346.	1.6	23
120	Low-Temperature Passivation of Amorphous-Silicon Thin-Film Transistors With Supercritical Fluids. IEEE Electron Device Letters, 2007, 28, 584-586.	2.2	23
121	On the Origin of Hole Valence Band Injection on GIFBE in PD SOI n-MOSFETs. IEEE Electron Device Letters, 2010, 31, 540-542.	2.2	23
122	Tri-Resistive Switching Behavior of Hydrogen Induced Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 217-219.	2.2	23
123	Role of H₂O Molecules in Passivation Layer of a-InGaZnO Thin Film Transistors. IEEE Electron Device Letters, 2017, 38, 469-472.	2.2	23
124	H2O adsorption on amorphous In-Ga-Zn-O thin-film transistors under negative bias stress. Applied Physics Letters, 2017, 111, .	1.5	23
125	Analysis of Negative Bias Temperature Instability Degradation in p-Type Low-Temperature Polycrystalline Silicon Thin-Film Transistors of Different Grain Sizes. IEEE Electron Device Letters, 2019, 40, 1768-1771.	2.2	23
126	Surface states related the bias stability of amorphous Inâ€“Gaâ€“Znâ€“O thin film transistors under different ambient gasses. Thin Solid Films, 2011, 520, 1432-1436.	0.8	22

#	Article	IF	Citations
127	Impact of static and dynamic stress on threshold voltage instability in high-k/metal gate n-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2011, 98, .	1.5	22
128	Application of in-cell touch sensor using photo-leakage current in dual gate a-InGaZnO thin-film transistors. Applied Physics Letters, 2012, 101, .	1.5	22
129	Engineering interface-type resistance switching based on forming current compliance in ITO/Ga2O3:ITO/TiN resistance random access memory: Conduction mechanisms, temperature effects, and electrode influence. Applied Physics Letters, 2016, 109, .	1.5	21
130	Research on Temperature Effect in Insulatorâ€“Metal Transition Selector Based on NbO_{<italic>x</italic>} Thin Films. IEEE Transactions on Electron Devices, 2018, 65, 5448-5452.	1.6	21
131	Drain-Induced-Barrier-Lowing-Like Effect Induced by Oxygen-Vacancy in Scaling-Down via-Contact Type Amorphous InGaZnO Thin-Film Transistors. IEEE Journal of the Electron Devices Society, 2018, 6, 685-690.	1.2	21
132	Investigation of the Capacitanceâ€“Voltage Electrical Characteristics of Thin-Film Transistors Caused by Hydrogen Diffusion under Negative Bias Stress in a Moist Environment. ACS Applied Materials & Interfaces, 2019, 11, 40196-40203.	4.0	21
133	Gate Modulation of Excitatory and Inhibitory Synaptic Plasticity in a Low-Temperature Polysilicon Thin Film Synaptic Transistor. ACS Applied Electronic Materials, 2019, 1, 132-140.	2.0	21
134	Physical and electrical characteristics of Ba(Zr0.1Ti0.9)O3 thin films under oxygen plasma treatment for applications in nonvolatile memory devices. Applied Physics A: Materials Science and Processing, 2007, 90, 329-331.	1.1	20
135	Low temperature improvement method on characteristics ofÂBa(Zr0.1Ti0.9)O3 thin films deposited on indium tin oxide/glass substrates. Applied Physics A: Materials Science and Processing, 2010, 99, 291-295.	1.1	20
136	Investigating the improvement of resistive switching trends after post-forming negative bias stress treatment. Applied Physics Letters, 2011, 99, 132104.	1.5	20
137	Carrier Transport and Multilevel Switching Mechanism for Chromium Oxide Resistive Random-Access Memory. Electrochemical and Solid-State Letters, 2011, 14, H103.	2.2	20
138	High-stability oxygen sensor based on amorphous zinc tin oxide thin film transistor. Applied Physics Letters, 2012, 100, .	1.5	20
139	Hopping conduction distance dependent activation energy characteristics of Zn:SiO2 resistance random access memory devices. Applied Physics Letters, 2013, 102, .	1.5	20
140	Investigation of a Hump Phenomenon in Back-Channel-Etched Amorphous In-Ga-Zn-O Thin-Film Transistors Under Negative Bias Stress. IEEE Electron Device Letters, 2017, 38, 592-595.	2.2	20
141	Model of dielectric breakdown in hafnia-based ferroelectric capacitors. Journal of Applied Physics, 2018, 124, .	1.1	20
142	Nonvolatile memory characteristics of nickel-silicon-nitride nanocrystal. Applied Physics Letters, 2007, 91, 082103.	1.5	19
143	Charge storage characteristics of Mo nanocrystal dependence on Mo oxide reduction. Applied Physics Letters, 2008, 93, 222101.	1.5	19
144	Mechanism of Triple Ions Effect in GeSO Resistance Random Access Memory. IEEE Electron Device Letters, 2015, 36, 552-554.	2.2	19

#	Article	IF	Citations
145	Effects of plasma treatment time on surface characteristics of indium-tin-oxide film for resistive switching storage applications. Applied Surface Science, 2017, 414, 224-229.	3.1	19
146	Solving the Scaling Issue of Increasing Forming Voltage in Resistive Random Access Memory Using Highâ€k Spacer Structure. Advanced Electronic Materials, 2017, 3, 1700171.	2.6	19
147	High-Voltage Backside-Illuminated CMOS Photovoltaic Module for Powering Implantable Temperature Sensors. IEEE Journal of Photovoltaics, 2018, 8, 342-347.	1.5	19
148	Reducing Forming Voltage by Applying Bipolar Incremental Step Pulse Programming in a 1T1R Structure Resistance Random Access Memory. IEEE Electron Device Letters, 2018, 39, 815-818.	2.2	19
149	Reconfigurable logic in nanosecond Cu/GeTe/TiN filamentary memristors for energy-efficient in-memory computing. Nanotechnology, 2018, 29, 385203.	1.3	19
150	Broadband Optoelectronic Synaptic Thinâ€Film Transistors Based on Oxide Semiconductors. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900630.	1.2	19
151	Improvement of Resistive Switching Characteristics in Zinc Oxide-Based Resistive Random Access Memory by Ammoniation Annealing. IEEE Electron Device Letters, 2020, 41, 357-360.	2.2	19
152	Fabrication of One-Transistor-Capacitor Structure of Nonvolatile TFT Ferroelectric RAM Devices Using Ba(Zr_{0.1}Ti_{0.9})O₃ Gated Oxide Film. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2007, 54, 1726-1730.	1.7	18
153	On the Origin of Gate-Induced Floating-Body Effect in PD SOI p-MOSFETs. IEEE Electron Device Letters, 2011, 32, 847-849.	2.2	18
154	H2O-Assisted O2 Adsorption in Sol-Gel Derived Amorphous Indium Gallium Zinc Oxide Thin Film Transistors. Electrochemical and Solid-State Letters, 2011, 14, H235.	2.2	18
155	Low-Temperature Synthesis of ZnO Nanotubes by Supercritical CO2 Fluid Treatment. Electrochemical and Solid-State Letters, 2011, 14, K47.	2.2	18
156	The asymmetrical degradation behavior on drain bias stress under illumination for InGaZnO thin film transistors. Applied Physics Letters, 2012, 100, .	1.5	18
157	High performance of graphene oxide-doped silicon oxide-based resistance random access memory. Nanoscale Research Letters, 2013, 8, 497.	3.1	18
158	Formation of Ge nanocrystals using Si1.33Ge0.67O2 and Si2.67Ge1.33N2 film for nonvolatile memory application. Applied Physics Letters, 2007, 91, .	1.5	17
159	Role of germanium in the reduced temperature dependence of Ti-based nanocrystals formation for nonvolatile memory applications. Applied Physics Letters, 2009, 95, 262110.	1.5	17
160	Enhanced retention characteristic of NiSi2/SiNx compound nanocrystal memory. Applied Physics Letters, 2010, 96, .	1.5	17
161	Paraffin wax passivation layer improvements in electrical characteristics of bottom gate amorphous indiumâ€“galliumâ€“zinc oxide thin-film transistors. Thin Solid Films, 2011, 520, 1608-1611.	0.8	17
162	Impact of Mechanical Strain on GIFBE in PD SOI p-MOSFETs as Indicated From NBTI Degradation. IEEE Electron Device Letters, 2012, 33, 303-305.	2.2	17

#	Article	IF	Citations
163	Improvement of Resistive Switching Characteristics by Thermally Assisted Forming Process for $hbox{SiO}_{2}$-Based Structure. IEEE Electron Device Letters, 2013, 34, 226-228.	2.2	17
164	Investigating the degradation behavior under hot carrier stress for InGaZnO TFTs with symmetric and asymmetric structures. Thin Solid Films, 2013, 528, 57-60.	0.8	17
165	Influence of molybdenum doping on the switching characteristic in silicon oxide-based resistive switching memory. Applied Physics Letters, 2013, 102, .	1.5	17
166	Effect of different constant compliance current for hopping conduction distance properties of the Sn:SiOx thin film RRAM devices. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	17
167	Ultra-Low Switching Voltage Induced by Inserting SiO₂Layer in Indiumâ€“Tinâ€“Oxide-Based Resistance Random Access Memory. IEEE Electron Device Letters, 2016, 37, 1276-1279.	2.2	17
168	Approaching Defect-free Amorphous Silicon Nitride by Plasma-assisted Atomic Beam Deposition for High Performance Gate Dielectric. Scientific Reports, 2016, 6, 28326.	1.6	17
169	Effect of SiO₂ Buffer Layer Thickness on Performance and Reliability of Flexible Polycrystalline Silicon TFTs Fabricated on Polyimide. IEEE Electron Device Letters, 2016, 37, 1578-1581.	2.2	17
170	Abnormal hump in capacitanceâ€“voltage measurements induced by ultraviolet light in a-IGZO thin-film transistors. Applied Physics Letters, 2017, 110, .	1.5	17
171	Abnormal Dual Channel Formation Induced by Hydrogen Diffusion From SiN_xInterlayer Dielectric in Top Gate a-InGaZnO Transistors. IEEE Electron Device Letters, 2017, 38, 334-337.	2.2	17
172	Investigation of an anomalous hump phenomenon in via-type amorphous In-Ga-Zn-O thin-film transistors under positive bias temperature stress. Applied Physics Letters, 2017, 110, .	1.5	17
173	Boolean and Sequential Logic in a Oneâ€Memristorâ€Oneâ€Resistor (1M1R) Structure for Inâ€Memory Computing. Advanced Electronic Materials, 2018, 4, 1800229.	2.6	17
174	Analyzing Electric Field Effect by Applying an Ultra-Short Time Pulse Condition in Hafnium Oxide-Based RRAM. IEEE Electron Device Letters, 2018, 39, 1163-1166.	2.2	17
175	Enhancing the Electrical Uniformity and Reliability of the HfO₂-Based RRAM Using High-Permittivity Ta₂O₅ Side Wall. IEEE Journal of the Electron Devices Society, 2018, 6, 627-632.	1.2	17
176	A Novel Heat Dissipation Structure for Inhibiting Hydrogen Diffusion in Top-Gate a-InGaZnO TFTs. IEEE Electron Device Letters, 2019, 40, 1447-1450.	2.2	17
177	Inâ€Memory Hamming Weight Calculation in a 1T1R Memristive Array. Advanced Electronic Materials, 2020, 6, 2000457.	2.6	17
178	Improvement of Hydrogenated Amorphous-Silicon TFT Performances With Low-kSiloxane-Based Hydrogen Silsesquioxane (HSQ) Passivation Layer. IEEE Electron Device Letters, 2006, 27, 902-904.	2.2	16
179	Effects of Supercritical Fluids Activation on Carbon Nanotube Field Emitters. IEEE Nanotechnology Magazine, 2007, 6, 29-34.	1.1	16
180	Formation and nonvolatile memory characteristics of multilayer nickel-silicide NCs embedded in nitride layer. Journal of Applied Physics, 2008, 104, 094303.	1.1	16

#	Article	IF	Citations
181	Reproducible resistance switching of a relatively thin FeOx layer produced by oxidizing the surface of a FePt electrode in a metal-oxideâ€“metal structure. Thin Solid Films, 2010, 519, 1536-1539.	0.8	16
182	Space electric field concentrated effect for Zr:SiO2 RRAM devices using porous SiO2 buffer layer. Nanoscale Research Letters, 2013, 8, 523.	3.1	16
183	Asymmetric structure-induced hot-electron injection under hot-carrier stress in a-InGaZnO thin film transistor. Applied Physics Letters, 2013, 103, .	1.5	16
184	H₂O Induced Hump Phenomenon in Capacitanceâ€“Voltage Measurements of a-IGZO Thin-Film Transistors. IEEE Transactions on Device and Materials Reliability, 2016, 16, 20-24.	1.5	16
185	Interconversion Between Bipolar and Complementary Behavior in Nanoscale Resistive Switching Devices. IEEE Transactions on Electron Devices, 2019, 66, 619-624.	1.6	16
186	Abnormal Hump Effect Induced by Hydrogen Diffusion During Self-Heating Stress in Top-Gate Amorphous InGaZnO TFTs. IEEE Transactions on Electron Devices, 2020, 67, 2807-2811.	1.6	16
187	In-Memory Digital Comparator Based on a Single Multivalued One-Transistor-One-Resistor Memristor. IEEE Transactions on Electron Devices, 2020, 67, 1293-1296.	1.6	16
188	Low temperature defect passivation technology for semiconductor electronic devicesâ€”supercritical fluids treatment process. Materials Today Physics, 2020, 14, 100225.	2.9	16
189	Anomalous Capacitance Induced by GIDL in P-Channel LTPS TFTs. IEEE Electron Device Letters, 2009, 30, 1179-1181.	2.2	15
190	Performance enhancement of a novel P-type junctionless transistor using a hybrid poly-Si fin channel. , 2014, , .		15
191	Ultralow Power Resistance Random Access Memory Device and Oxygen Accumulation Mechanism in an Indiumâ€“Tin-Oxide Electrode. IEEE Transactions on Electron Devices, 2016, 63, 4737-4743.	1.6	15
192	Systematic Analysis of High-Current Effects in Flexible Polycrystalline-Silicon Transistors Fabricated on Polyimide. IEEE Transactions on Electron Devices, 2017, 64, 3167-3173.	1.6	15
193	Cyclical Annealing Technique To Enhance Reliability of Amorphous Metal Oxide Thin Film Transistors. ACS Applied Materials & Interfaces, 2018, 10, 25866-25870.	4.0	15
194	A Novel Self-Aligned Etch-Stopper Structure With Lower Photo Leakage for AMLCD and Sensor Applications. IEEE Electron Device Letters, 2006, 27, 978-980.	2.2	14
195	Application of the low dielectric methyl-silsesquiazane (MSZ) as a passivation layer on TFT-LCD. Thin Solid Films, 2006, 515, 1117-1120.	0.8	14
196	Formation of germanium nanocrystals embedded in silicon-oxygen-nitride layer. Applied Physics Letters, 2006, 89, 052112.	1.5	14
197	Enhanced gate-induced floating-body effect in PD SOI MOSFET under external mechanical strain. Surface and Coatings Technology, 2010, 205, 1470-1474.	2.2	14
198	The resistive switching characteristics in TaON films for nonvolatile memory applications. Thin Solid Films, 2013, 528, 224-228.	0.8	14

#	Article	IF	Citations
199	Insertion of a Si layer to reduce operation current for resistive random access memory applications. Applied Physics Letters, 2013, 102, .	1.5	14
200	Reduction of defect formation in amorphous indium-gallium-zinc-oxide thin film transistors by N2O plasma treatment. Journal of Applied Physics, 2013, 114, .	1.1	14
201	Analysis of Contrasting Degradation Behaviors in Channel and Drift Regions Under Hot Carrier Stress in PDSOI LD N-Channel MOSFETs. IEEE Electron Device Letters, 2017, 38, 705-707.	2.2	14
202	Suppression of endurance degradation by applying constant voltage stress in one-transistor and one-resistor resistive random access memory. Japanese Journal of Applied Physics, 2017, 56, 010303.	0.8	14
203	Optimal Tuning of Memristor Conductance Variation in Spiking Neural Networks for Online Unsupervised Learning. IEEE Transactions on Electron Devices, 2019, 66, 2844-2849.	1.6	14
204	Improvement of electrical characteristics for fluorine-ion-implanted poly-Si TFTs using ELC. IEEE Electron Device Letters, 2006, 27, 262-264.	2.2	13
205	Effect of N2O plasma treatment on the improvement of instability under light illumination for InGaZnO thin-film transistors. Thin Solid Films, 2011, 520, 1427-1431.	0.8	13
206	Charge trapping induced drain-induced-barrier-lowering in HfO2/TiN p-channel metal-oxide-semiconductor-field-effect-transistors under hot carrier stress. Applied Physics Letters, 2012, 100, .	1.5	13
207	Oxygen-Adsorption-Induced Anomalous Capacitance Degradation in Amorphous Indium-Gallium-Zinc-Oxide Thin-Film-Transistors under Hot-Carrier Stress. Journal of the Electrochemical Society, 2012, 159, H286-H289.	1.3	13
208	Impact of Electroforming Current on Self-Compliance Resistive Switching in an ${m ITO}/{m Gd{:}SiO}_{m x}/{m TiN}$ Structure. IEEE Electron Device Letters, 2013, 34, 858-860.	2.2	13
209	Investigation of an anomalous hump in gate current after negative-bias temperature-instability in HfO2/metal gate p-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2013, 102, .	1.5	13
210	Nitrogen Buffering Effect on Oxygen in Indium-Tin-Oxide-Capped Resistive Random Access Memory With NH₃ Treatment. IEEE Electron Device Letters, 2015, 36, 1138-1141.	2.2	13
211	The effect of asymmetrical electrode form after negative bias illuminated stress in amorphous IGZO thin film transistors. Applied Physics Letters, 2017, 110, .	1.5	13
212	Impact of repeated uniaxial mechanical strain on flexible a-IGZO thin film transistors with symmetric and asymmetric structures. Applied Physics Letters, 2017, 110, 263505.	1.5	13
213	Controllable Functional Layer and Temperature-Dependent Characteristic in Niobium Oxide Insulatorâ€“Metal Transition Selector. IEEE Transactions on Electron Devices, 2020, 67, 2771-2777.	1.6	13
214	Improvement of the performance of ZnO TFTs by low-temperature supercritical fluid technology treatment. Surface and Coatings Technology, 2009, 204, 1112-1115.	2.2	12
215	Photoelectric heat effect induce instability on the negative bias temperature illumination stress for InGaZnO thin film transistors. Applied Physics Letters, 2012, 101, .	1.5	12
216	Controllable Set Voltage in Bilayer ZnO:SiO‹sub›2‹/sub›/ZnO‹sub›‹italic›x‹/italic›‹/sub› Resistance Random Access Memory by Oxygen Concentration Gradient Manipulation. IEEE Electron Device Letters, 2014, 35, 1227-1229.	2.2	12

#	Article	IF	Citations
217	Improvement of Bipolar Switching Properties of Gd:SiOx RRAM Devices on Indium Tin Oxide Electrode by Low-Temperature Supercritical CO2 Treatment. Nanoscale Research Letters, 2016, 11, 52.	3.1	12
218	Illumination Effect on Bipolar Switching Properties of Gd:SiO2 RRAM Devices Using Transparent Indium Tin Oxide Electrode. Nanoscale Research Letters, 2016, 11, 224.	3.1	12
219	Localized tail state distribution and hopping transport in ultrathin zinc-tin-oxide thin film transistor. Applied Physics Letters, 2017, 110, .	1.5	12
220	Enhancement of Surface Chemical and Physical Properties of Germaniumâ€“Sulfur Thin Film Using a Waterâ€Supplemented Carbon Dioxide Supercritical Fluid Treatment Technique. Advanced Materials Interfaces, 2018, 5, 1801105.	1.9	12
221	Hydrogen as a Cause of Abnormal Subchannel Formation Under Positive Bias Temperature Stress in a-InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2019, 66, 2954-2959.	1.6	12
222	Multiâ€Functional Controllable Memory Devices Applied for 3D Integration Based on a Single Niobium Oxide Layer. Advanced Electronic Materials, 2020, 6, 1900756.	2.6	12
223	Forming-free, ultra-high on-state current, and self-compliance selector based on titanium-doped NbOx thin films. Ceramics International, 2021, 47, 22677-22682.	2.3	12
224	Performance enhancement of ZnGa2O4 Schottky type deep-ultraviolet photodetectors by oxygen supercritical fluid treatment. Results in Physics, 2021, 29, 104764.	2.0	12
225	Advanced Low-Temperatureâ€“High-Pressure Hydrogen Treatment for Interface Defect Passivation in Si- and SiGe-Channel MOSCAPs. IEEE Transactions on Electron Devices, 2020, 67, 5403-5407.	1.6	12
226	High-performance metal-induced lateral-crystallization polysilicon thin-film transistors with multiple nanowire channels and multiple gates. IEEE Nanotechnology Magazine, 2006, 5, 157-162.	1.1	11
227	Investigation of the low dielectric siloxane-based hydrogen silsesquioxane (HSQ) as passivation layer on TFT-LCD. Thin Solid Films, 2007, 516, 374-377.	0.8	11
228	Application of Supercritical CO[sub 2] Fluid for Dielectric Improvement of SiO[sub x] Film. Electrochemical and Solid-State Letters, 2009, 12, H35.	2.2	11
229	Resistive switching characteristics of ytterbium oxide thin film for nonvolatile memory application. Thin Solid Films, 2011, 520, 1656-1659.	0.8	11
230	Enhancement of the stability of resistive switching characteristics by conduction path reconstruction. Applied Physics Letters, 2013, 103, 042902.	1.5	11
231	Mechanism of power consumption inhibitive multi-layer Zn:SiO2/SiO2structure resistance random access memory. Journal of Applied Physics, 2013, 114, 234501.	1.1	11
232	Confirmation of filament dissolution behavior by analyzing electrical field effect during reset process in oxide-based RRAM. Applied Physics Letters, 2016, 109, .	1.5	11
233	Effects of erbium doping of indium tin oxide electrode in resistive random access memory. Applied Physics Express, 2016, 9, 034202.	1.1	11
234	Effect of charge quantity on conduction mechanism of high- and low-resistance states during forming process in a one-transistorâ€“one-resistor resistance random access memory. Applied Physics Express, 2017, 10, 054101.	1.1	11

#	Article	IF	Citations
235	Super Critical Fluid Technique to Enhance Current Output on Amorphous Silicon-Based Photovoltaic. IEEE Electron Device Letters, 2017, 38, 1401-1404.	2.2	11
236	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at ${R} = 2$ mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 913-916.	2.2	11
237	Inhibiting the Kink Effect and Hot-Carrier Stress Degradation Using Dual-Gate Low-Temperature Poly-Si TFTs. IEEE Electron Device Letters, 2020, 41, 54-57.	2.2	11
238	Abnormal High Resistive State Current Mechanism Transformation in Ti/HfO₂/TiN Resistive Random Access Memory. IEEE Electron Device Letters, 2020, 41, 224-227.	2.2	11
239	A high-speed MIM resistive memory cell with an inherent vanadium selector. Applied Materials Today, 2020, 21, 100848.	2.3	11
240	Origin of High Current and Illumination Stress Instability in Self-Aligned a-InGaZnO Thin Film Transistors With Al₂O₃ as High-Î° Gate Dielectric. IEEE Electron Device Letters, 2020, 41, 565-568.	2.2	11
241	Cryptographic Key Generation and In Situ Encryption in Oneâ€Transistorâ€Oneâ€Resistor Memristors for Hardware Security. Advanced Electronic Materials, 2021, 7, 2001182.	2.6	11
242	Improved reliability of Mo nanocrystal memory with ammonia plasma treatment. Applied Physics Letters, 2009, 94, 062106.	1.5	10
243	Mechanism and characterizations studies of resistive switching effects on a thin FeOx-transition layer of the Ti/TiN/SiO2/FeOx/FePt structure by thermal annealing treatments. Materials Chemistry and Physics, 2011, 131, 262-267.	2.0	10
244	Study of Electric Faucet Structure by Embedding Co Nanocrystals in a FeO_x-Based Memristor. ECS Journal of Solid State Science and Technology, 2012, 1, Q57-Q61.	0.9	10
245	Abnormal Subthreshold Leakage Current at High Temperature in InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2012, 33, 540-542.	2.2	10
246	Investigation of temperature-dependent asymmetric degradation behavior induced by hot carrier effect in oxygen ambiance in Inâ€“Gaâ€“Zn-O thin film transistors. Thin Solid Films, 2014, 572, 33-38.	0.8	10
247	Impact of Forming Compliance Current on Storage Window Induced by a Gadolinium Electrode in Oxide-Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2018, 65, 96-100.	1.6	10
248	A Dualâ€Gate InGaZnO₄â€Based Thinâ€Film Transistor for Highâ€Sensitivity UV Detection. Advanced Materials Technologies, 2019, 4, 1900106.	3.0	10
249	Enhancing LiAlO_X synaptic performance by reducing the Schottky barrier height for deep neural network applications. Nanoscale, 2020, 12, 22970-22977.	2.8	10
250	A Novel Structure to Reduce Degradation Under Mechanical Bending in Foldable Low Temperature Polysilicon TFTs Fabricated on Polyimide. IEEE Electron Device Letters, 2020, 41, 725-728.	2.2	10
251	Improving Performance by Inserting an Indium Oxide Layer as an Oxygen Ion Storage Layer in HfOâ„‚-Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2021, 68, 1037-1040.	1.6	10
252	Obtaining impact ionization-induced hole current by electrical measurements in gallium nitride metalâ€“insulatorâ€“semiconductor high electron mobility transistors. Journal Physics D: Applied Physics, 2021, 54, 285104.	1.3	10

#	Article	IF	Citations
253	Investigating Selectorless Property within Niobium Devices for Storage Applications. ACS Applied Materials & Interfaces, 2022, 14, 2343-2350.	4.0	10
254	Reduction of leakage current in metal-induced lateral crystallization polysilicon TFTs with dual-gate and multiple nanowire channels. IEEE Electron Device Letters, 2005, 26, 646-648.	2.2	9
255	Integration issues for siloxane-based hydrogen silsesquioxane (HSQ) applied on TFT-LCDs. Thin Solid Films, 2006, 498, 70-74.	0.8	9
256	Low temperature improvement on silicon oxide grown by electron-gun evaporation for resistance memory applications. Applied Physics Letters, 2008, 93, 052903.	1.5	9
257	Formation and Nonvolatile Memory Application of Ge Nanocrystals by Using Internal Competition Reaction of $hbox{Si}_{{f 1.33}} hbox{Ge}_{{f 0.67}} hbox{O}_{f 2}$ and $hbox{Si}_{{f 2.67}} hbox{Ge}_{{f 1.33}} hbox{N}_{f 2}$ Layers. IEEE Nanotechnology Magazine, 2009, 8, 185-189.	1.1	9
258	Nonvolatile memory effect of tungsten nanocrystals under oxygen plasma treatments. Thin Solid Films, 2010, 518, 7339-7342.	0.8	9
259	Charge trapping induced frequency-dependence degradation in n-MOSFETs with high-k/metal gate stacks. Thin Solid Films, 2011, 520, 1511-1515.	0.8	9
260	The suppressed negative bias illumination-induced instability in In-Ga-Znâ€“O thin film transistors with fringe field structure. Applied Physics Letters, 2012, 101, .	1.5	9
261	Characterization of environment-dependent hysteresis in indium gallium zinc oxide thin film transistors. Surface and Coatings Technology, 2013, 231, 531-534.	2.2	9
262	Investigation of carrier transport behavior in amorphous indiumâ€“galliumâ€“zinc oxide thin film transistors. Japanese Journal of Applied Physics, 2015, 54, 094101.	0.8	9
263	Complementary resistive switching behavior for conductive bridge random access memory. Applied Physics Express, 2016, 9, 064201.	1.1	9
264	Obtaining Lower Forming Voltage and Self-Compliance Current by Using a Nitride Gas/Indiumâ€“Tin Oxide Insulator in Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2016, 63, 4769-4775.	1.6	9
265	Competing weak localization and weak antilocalization in amorphous indiumâ€“galliumâ€“zinc-oxide thin-film transistors. Applied Physics Letters, 2017, 110, .	1.5	9
266	Effects of Mechanical Stress on Flexible Dualâ€Gate aâ€InGaZnO Thinâ€Film Transistors. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700426.	0.8	9
267	Impact of Dehydrogenation Annealing Process Temperature on Reliability of Polycrystalline Silicon Thin Film Transistors. IEEE Electron Device Letters, 2019, 40, 1638-1641.	2.2	9
268	Effect of ELA Energy Density on Self-Heating Stress in Low-Temperature Polycrystalline Silicon Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3163-3166.	1.6	9
269	Effects of Redundant Electrode Width on Stability of a-InGaZnO Thin-Film Transistors Under Hot-Carrier Stress. IEEE Transactions on Electron Devices, 2020, 67, 2372-2375.	1.6	9
270	Ultrahigh Uniformity and Stability in NbO_x-Based Selector for 3-D Memory by Using Ru Electrode. IEEE Transactions on Electron Devices, 2021, 68, 2255-2259.	1.6	9

#	Article	IF	Citations
271	Investigation of Thermal Behavior on High-Performance Organic TFTs Using Phase Separated Organic Semiconductors. IEEE Electron Device Letters, 2021, 42, 859-862.	2.2	9
272	Investigation on the current conduction mechanism of HfZrO_x ferroelectric memory. Journal Physics D: Applied Physics, 2020, 53, 445110.	1.3	9
273	A study of parasitic resistance effects in thin-channel polycrystalline silicon TFTs with tungsten-clad source/drain. IEEE Electron Device Letters, 2003, 24, 509-511.	2.2	8
274	Formation of cobalt-silicide nanocrystals in Ge-doped dielectric layer for the application on nonvolatile memory. Applied Physics Letters, 2008, 92, 152115.	1.5	8
275	Cobalt nanodots formed by annealing the CoSiO layer for the application of the nonvolatile memory. Applied Physics Letters, 2009, 94, 102106.	1.5	8
276	Formation and nonvolatile memory characteristics of W nanocrystals by in-situ steam generation oxidation. Thin Solid Films, 2010, 519, 1677-1680.	0.8	8
277	Analysis of Degradation Mechanism in SONOS-TFT Under Hot-Carrier Operation. IEEE Electron Device Letters, 2010, 31, 1413-1415.	2.2	8
278	Improving Resistance Switching Characteristics with SiGeOx/SiGeON Double Layer for Nonvolatile Memory Applications. Electrochemical and Solid-State Letters, 2011, 14, H419.	2.2	8
279	Role of InGaOx resistive switching characteristics on the performances of resistance random access memory of Pt/IGO/TiN device. Thin Solid Films, 2013, 528, 26-30.	0.8	8
280	Influence of forming process on resistance switching characteristics of In2O3/SiO2 bi-layer. Thin Solid Films, 2013, 528, 31-35.	0.8	8
281	Analyzing the effects of ambient dependence for InGaZnO TFTs under illuminated bias stress. Surface and Coatings Technology, 2013, 231, 465-470.	2.2	8
282	Influence of Oxygen Concentration on Self-Compliance RRAM in Indium Oxide Film. IEEE Electron Device Letters, 2014, 35, 909-911.	2.2	8
283	Improvements in the reliability of a-InGaZnO thin-film transistors with triple stacked gate insulator in flexible electronics applications. Thin Solid Films, 2015, 595, 176-180.	0.8	8
284	The effect of device electrode geometry on performance after hot-carrier stress in amorphous In-Ga-Zn-O thin film transistors with different via-contact structures. Applied Physics Letters, 2017, 110, .	1.5	8
285	Overcoming Limited Resistance in 1T1R RRAM Caused by Pinch-Off Voltage During Reset Process. IEEE Transactions on Electron Devices, 2019, 66, 4706-4709.	1.6	8
286	A comprehensive study of enhanced characteristics with localized transition in interface-type vanadium-based devices. Materials Today Physics, 2020, 13, 100201.	2.9	8
287	Enhancement of Mechanical Bending Stress Endurance Using an Organic Trench Structure in Foldable Polycrystalline Silicon TFTs. IEEE Electron Device Letters, 2020, 41, 721-724.	2.2	8
288	Incorporation of Resistive Random Access Memory into Lowâ€Temperature Polysilicon Transistor with Finâ€Like Structure as 1T1R Device. Advanced Electronic Materials, 2020, 6, 2000066.	2.6	8

#	Article	IF	Citations
289	Degradation Behavior of Etch-Stopper-Layer Structured a-InGaZnO Thin-Film Transistors Under Hot-Carrier Stress and Illumination. IEEE Transactions on Electron Devices, 2021, 68, 556-559.	1.6	8
290	Realizing forming-free characteristic by doping Ag into HfO₂-based RRAM. Applied Physics Express, 2021, 14, 041008.	1.1	8
291	Comprehensive Regulation of the Threshold Oscillation for Neuromorphic Systems Based on Cryogenic Performance of NbOâ„ Device. IEEE Electron Device Letters, 2021, 42, 692-695.	2.2	8
292	Suppression of Edge Effect Induced by Positive Gate Bias Stress in Low-Temperature Polycrystalline Silicon TFTs With Channel Width Extension Over Source/Drain Regions. IEEE Transactions on Electron Devices, 2020, 67, 5552-5556.	1.6	8
293	The Co-Improvement of Selectivity and Uniformity on NbOâ„"-Based Selector by Al-Doping. IEEE Electron Device Letters, 2022, 43, 870-873.	2.2	8
294	Heterogeneous metal oxide channel structure for ultra-high sensitivity phototransistor with modulated operating conditions. Journal of Materials Chemistry C, 2022, 10, 9192-9197.	2.7	8
295	High performance and high reliability polysilicon thin-filmiyansistors with multiple nano-wire channels. , 0, , .		7
296	Improvement on low-temperature deposited HfO2 film and interfacial layer by high-pressure oxygen treatment. Solid-State Electronics, 2011, 62, 128-131.	0.8	7
297	Study of Resistive Switching Characteristics on a Temperature-Sensitive FeOx-Transition Layer in a TiN/SiO2/FeOx/Fe Structure. ECS Journal of Solid State Science and Technology, 2012, 1, Q91-Q95.	0.9	7
298	Characterization and Investigation of a Hot-Carrier Effect in Via-Contact Type a-InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2013, 60, 1681-1688.	1.6	7
299	High-k shallow traps observed by charge pumping with varying discharging times. Journal of Applied Physics, 2013, 114, 174506.	1.1	7
300	Low power consumption resistance random access memory with Pt/InOx/TiN structure. Applied Physics Letters, 2013, 103, 102903.	1.5	7
301	Dual operation characteristics of resistance random access memory in indium-gallium-zinc-oxide thin film transistors. Applied Physics Letters, 2014, 104, .	1.5	7
302	Investigation of abnormal negative threshold voltage shift under positive bias stress in input/output n-channel metal-oxide-semiconductor field-effect transistors with TiN/HfO2 structure using fast I-V measurement. Applied Physics Letters, 2014, 104, .	1.5	7
303	Influence of Thermal Annealing Treatment on Bipolar Switching Properties of Vanadium Oxide Thin-Film Resistance Random-Access Memory Devices. Journal of Electronic Materials, 2017, 46, 2147-2152.	1.0	7
304	Design, Properties, and TFT Application of Solutionâ€Processed Inâ€Gaâ€Cdâ€O Thin Films. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800034.	1.2	7
305	Floating top gate-induced output enhancement of a-InGaZnO thin film transistors under single gate operations. Applied Physics Letters, 2018, 113, .	1.5	7
306	Improving Reliability of High-Performance Ultraviolet Sensor in a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 1455-1458.	2.2	7

#	Article	IF	Citations
307	Heterojunction Channels in Oxide Semiconductors for Visibleâ€Blind Nonvolatile Optoelectronic Memories. Advanced Electronic Materials, 2020, 6, 2000747.	2.6	7
308	Enhancing Threshold Switching Characteristics and Stability of Vanadium Oxide-Based Selector With Vanadium Electrode. IEEE Transactions on Electron Devices, 2020, 67, 5059-5062.	1.6	7
309	Total-Dose Effect of X-ray Irradiation on Low-Temperature Polycrystalline Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2020, 41, 864-867.	2.2	7
310	Analysis of Edge Effect Occurring in Non-Volatile Ferroelectric Transistors. IEEE Electron Device Letters, 2021, 42, 315-318.	2.2	7
311	Gate Dielectric Breakdown in A-InGaZnO Thin Film Transistors With Cu Electrodes. IEEE Electron Device Letters, 2021, 42, 851-854.	2.2	7
312	Performance Improvement by Modifying Deposition Temperature in HfZrO_x Ferroelectric Memory. IEEE Transactions on Electron Devices, 2021, 68, 3838-3842.	1.6	7
313	Impact of electrode thermal conductivity on high resistance state level in HfO₂-based RRAM. Journal Physics D: Applied Physics, 2020, 53, 395101.	1.3	7
314	Formation of germanium nanocrystals by rapid thermal oxidizing SiGeO layer for nonvolatile memory application. Surface and Coatings Technology, 2007, 202, 1333-1337.	2.2	6
315	Charge Storage Characteristics of Mo Nanocrystal Memory Influenced by Ammonia Plasma Treatment. Journal of the Electrochemical Society, 2009, 156, H716.	1.3	6
316	High Density Ni Nanocrystals Formed by Coevaporating Ni and SiO[sub 2] Pellets for the Nonvolatile Memory Device Application. Electrochemical and Solid-State Letters, 2010, 13, H49.	2.2	6
317	Hole injection-reduced hot carrier degradation in n-channel metal-oxide-semiconductor field-effect-transistors with high-k gate dielectric. Applied Physics Letters, 2013, 102, 073507.	1.5	6
318	Mechanical stress influence on electronic transport in low-k SiOC dielectric single damascene capacitor. Applied Physics Letters, 2013, 102, .	1.5	6
319	Investigation of extra traps measured by charge pumping technique in high voltage zone in p-channel metal-oxide-semiconductor field-effect transistors with HfO2/metal gate stacks. Applied Physics Letters, 2013, 102, 012106.	1.5	6
320	On the Origin of Anomalous Offâ€“Current Under Hot Carrier Stress in p-Channel DDDMOS Transistors With STI Structure. IEEE Electron Device Letters, 2014, 35, 651-653.	2.2	6
321	Investigation of Hydration Reaction-Induced Protons Transport in Etching-Stop a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2015, 36, 1050-1052.	2.2	6
322	Communicationâ€"Effects of Oxygen Concentration Gradient on Resistive Switching Behavior in Oxygen Vacancy-Rich Electrodes. ECS Journal of Solid State Science and Technology, 2016, 5, Q115-Q118.	0.9	6
323	Combined Effects of Light Illumination and Various Bottom Gate Length on the Instability of Via-Contact-Type Amorphous InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2018, 65, 533-536.	1.6	6
324	Tuning the nanostructures and optical properties of undoped and N-doped ZnO by supercritical fluid treatment. AIP Advances, 2018, 8, .	0.6	6

#	Article	IF	Citations
325	Investigating Material Changes at Different Gadolinium Doping Power Levels in Indium-Tin Oxide Intended for Use as an Insulator in Resistive Switching Memory. IEEE Transactions on Electron Devices, 2019, 66, 2595-2599.	1.6	6
326	Effects of Ultraviolet Light on the Dual-Sweep <inline-formula> <tex-math notation="LaTeX">I </tex-math> </inline-formula>â€“<inline-formula> <tex-math notation="LaTeX">V </tex-math> </inline-formula> Curve of a-InGaZnO₄ Thin-Film Transistor. IEEE Transactions on Electron Devices, 2019, 66, 1772-1777.	1.6	6
327	The influence of temperature on set voltage for different high resistance state in 1T1R devices. Applied Physics Express, 2019, 12, 024004.	1.1	6
328	Abnormal Increment Substrate Current After Hot Carrier Stress in n-FinFET. IEEE Electron Device Letters, 2020, 41, 15-18.	2.2	6
329	Improving Breakdown Voltage in AlGaN/GaN Metal-Insulator-Semiconductor HEMTs Through Electric-Field Dispersion Layer Material Selection. IEEE Transactions on Device and Materials Reliability, 2021, 21, 320-323.	1.5	6
330	Comparison of the Hot Carrier Degradation of N- and P-Type Fin Field-Effect Transistors in 14-nm Technology Nodes. IEEE Electron Device Letters, 2021, 42, 1420-1423.	2.2	6
331	Reducing Interface Traps with High Density Hydrogen Treatment to Increase Passivated Emitter Rear Contact Cell Efficiency. Nanoscale Research Letters, 2019, 14, 375.	3.1	6
332	Meridian study on the response current affected by electrical pulse and acupuncture. Nanoscale Research Letters, 2020, 15, 146.	3.1	6
333	NiSiGe nanocrystals for nonvolatile memory devices. Applied Physics Letters, 2009, 94, 062102.	1.5	5
334	Analysis of Anomalous Capacitance Induced by TAGIDL in p-Channel LTPS TFTs. Journal of the Electrochemical Society, 2010, 157, H1003.	1.3	5
335	On-Current Decrease After Erasing Operation in the Nonvolatile Memory Device With LDD Structure. IEEE Electron Device Letters, 2011, 32, 1038-1040.	2.2	5
336	Anomalous on-current and subthreshold swing improvement in low-temperature polycrystalline-silicon thin-film transistors under Gate bias stress. Applied Physics Letters, 2011, 98, .	1.5	5
337	N 2 O plasma treatment suppressed temperature-dependent sub-threshold leakage current of amorphous indiumâ€“galliumâ€“zinc-oxide thin film transistors. Surface and Coatings Technology, 2013, 231, 281-284.	2.2	5
338	Abnormal sub-threshold swing degradation under dynamic hot carrier stress in HfO₂/TiN n-channel metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2013, 103, 022106.	1.5	5
339	High performance, excellent reliability multifunctional graphene oxide doped memristor achieved by self-protect ive compliance current structure. , 2014, , .		5
340	Influence of an anomalous dimension effect on thermal instability in amorphous-InGaZnO thin-film transistors. Journal of Applied Physics, 2014, 116, 154508.	1.1	5
341	Anomalous degradation behaviors under illuminated gate bias stress in a-Si:H thin film transistor. Thin Solid Films, 2014, 572, 79-84.	0.8	5
342	Ultrahigh Sensitivity Self-Amplification Phototransistor Achieved by Automatic Energy Band Lowering Behavior. IEEE Transactions on Electron Devices, 2014, 61, 3186-3190.	1.6	5

#	Article	IF	Citations
343	Hopping conduction properties of the Sn:SiO X thin-film resistance random access memory devices induced by rapid temperature annealing procedure. Applied Physics A: Materials Science and Processing, 2015, 119, 1609-1613.	1.1	5
344	Modifying Indium-Tin-Oxide by Gas Cosputtering for Use as an Insulator in Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2016, 63, 4288-4294.	1.6	5
345	Adjustable built-in resistor on oxygen-vacancy-rich electrode-capped resistance random access memory. Applied Physics Express, 2016, 9, 104201.	1.1	5
346	Reducing operation voltages by introducing a low-kswitching layer in indiumâ€“tin-oxide-based resistance random access memory. Applied Physics Express, 2016, 9, 061501.	1.1	5
347	Gate Insulator Morphology-Dependent Reliability in Organic Thin-Film Transistors. IEEE Electron Device Letters, 2016, 37, 228-230.	2.2	5
348	Recovery of failed resistive switching random access memory devices by a low-temperature supercritical treatment. Applied Physics Express, 2017, 10, 064001.	1.1	5
349	Reliability Test Integrating Electrical and Mechanical Stress at High Temperature for a-InGaZnO Thin Film Transistors. IEEE Transactions on Device and Materials Reliability, 2019, 19, 433-436.	1.5	5
350	Investigation of the forming process under UV illumination in HfO₂-based resistance random access memory with a transparent electrode. Journal Physics D: Applied Physics, 2020, 53, 025104.	1.3	5
351	Investigating the Back-Channel Effect and Asymmetric Degradation Under Self-Heating Stress in Large Size a-InGaZnO TFTs. IEEE Electron Device Letters, 2020, 41, 58-61.	2.2	5
352	Improving a-InGaZnO TFTs Reliability by Optimizing Electrode Capping Structure Under Negative Bias Illumination Stress. IEEE Electron Device Letters, 2020, 41, 1221-1224.	2.2	5
353	Stabilizing resistive random access memory by constructing an oxygen reservoir with analyzed state distribution. Nanoscale, 2020, 12, 23532-23536.	2.8	5
354	Effect of deposition temperature on electrical properties of one-transistor-one-capacitor (1T1C) FeRAM devices. Applied Physics Letters, 2020, 117, .	1.5	5
355	Enhancing Hot-Carrier Reliability of Dual-Gate Low-Temperature Polysilicon TFTs by Increasing Lightly Doped Drain Length. IEEE Electron Device Letters, 2020, 41, 1524-1527.	2.2	5
356	Comparison of physical electrical conductivity and acupuncture de-qi sensation between stainless steel needling and supercritical fluid-treated needling. Biomedical Journal, 2021, 44, S267-S274.	1.4	5
357	Investigation of HCD- and NBTI-Induced Ultralow Electric Field GIDL in 14-nm Technology Node FinFETs. IEEE Transactions on Electron Devices, 2020, 67, 2697-2701.	1.6	5
358	Electrical Degradation of In Situ SiN/AlGaN/GaN MIS-HEMTs Caused by Dehydrogenation and Trap Effect Under Hot Carrier Stress. IEEE Transactions on Electron Devices, 2021, 68, 4283-4288.	1.6	5
359	Abnormal Two-Stage Degradation on P-Type Low-Temperature Polycrystalline-Silicon Thin-Film Transistor Under Hot Carrier Conditions. IEEE Electron Device Letters, 2022, 43, 721-724.	2.2	5
360	Abnormal On-Current Degradation Under Non-Conductive Stress in Contact Field Plate Lateral Double-Diffused Metal-Oxide- Semiconductor Transistor With 0.13-Î¼m Bipolar-CMOS-DMOS Technology. IEEE Electron Device Letters, 2022, 43, 769-772.	2.2	5

#	Article	IF	Citations
361	Abnormal Threshold Voltage Degradation Under Semi-On State Stress in Si₃N₄/AlGaN/GaN-HEMT. IEEE Electron Device Letters, 2022, 43, 1420-1423.	2.2	5
362	Passivation Effect of Poly-Si Thin-Film Transistors With Fluorine-Ion-Implanted Spacers. IEEE Electron Device Letters, 2008, 29, 603-605.	2.2	4
363	Temperature-dependent memory characteristics of siliconâ€“oxideâ€“nitrideâ€“oxideâ€“silicon thin-film-transistors. Thin Solid Films, 2010, 518, 3999-4002.	0.8	4
364	Charge-Trapping-Induced Parasitic Capacitance and Resistance in SONOS TFTs Under Gate Bias Stress. IEEE Electron Device Letters, 2011, 32, 321-323.	2.2	4
365	Influence of hydrogen plasma treatment on charge storage characteristics in high density tungsten nanocrystal nonvolatile memory. Thin Solid Films, 2011, 519, 3897-3901.	0.8	4
366	Analysis of an anomalous hump in gate current after dynamic negative bias stress in Hf_xZr_{1-x}O₂/metal gate p-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2012, 101, 052105.	1.5	4
367	Analysis of anomalous traps measured by charge pumping technique in HfO2/metal gate n-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2012, 101, 233509.	1.5	4
368	Investigation of gate-bias stress and hot-carrier stress-induced instability of InGaZnO thin-film transistors under different environments. Surface and Coatings Technology, 2013, 231, 478-481.	2.2	4
369	Abnormal temperature-dependent floating-body effect on Hot-Carrier Degradation in PDSOI n-MOSFETs. Thin Solid Films, 2014, 572, 39-43.	0.8	4
370	Surface scattering mechanisms of tantalum nitride thin film resistor. Nanoscale Research Letters, 2014, 9, 177.	3.1	4
371	The Manipulation of Temperature Coefficient Resistance of TaN Thin-Film Resistor by Supercritical CO₂ Fluid. IEEE Electron Device Letters, 2015, 36, 271-273.	2.2	4
372	Mechanisms of Low-Temperature Nitridation Technology on a TaN Thin Film Resistor for Temperature Sensor Applications. Nanoscale Research Letters, 2016, 11, 275.	3.1	4
373	Fast-IV Measurement Investigation of the Role of TiN Gate Nitrogen Concentration on Bulk Traps in HfO2 Layer in p-MOSFETs. IEEE Transactions on Device and Materials Reliability, 2017, 17, 475-478.	1.5	4
374	Weak Localization and Weak Antilocalization in Double-Gate a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2018, 39, 212-215.	2.2	4
375	Solution-processed Gaâ€“Cdâ€“O thin-films with tunable bandgaps and their transistors. Journal Physics D: Applied Physics, 2018, 51, 335101.	1.3	4
376	Indium Diffusion Behavior and Application in HfO 2 â€Based Conductive Bridge Random Access Memory. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900285.	1.2	4
377	An Energy-Band Model for Dual-Gate-Voltage Sweeping in Hydrogenated Amorphous Silicon Thin-Film Transistors. IEEE Transactions on Electron Devices, 2019, 66, 2614-2619.	1.6	4
378	Abnormal Relationship Between Hot Carrier Stress Degradation and Body Current in High-k Metal Gate in the 14-nm Node. IEEE Electron Device Letters, 2019, 40, 498-501.	2.2	4

#	Article	IF	Citations
379	Leakage Current in Fast Recovery Diode Suppressed by Low Temperature Supercritical Fluid Treatment Process. IEEE Electron Device Letters, 2020, 41, 1540-1543.	2.2	4
380	Abnormal hysteresis formation in hump region after positive gate bias stress in low-temperature poly-silicon thin film transistors. Journal Physics D: Applied Physics, 2020, 53, 405104.	1.3	4
381	Effects of X-ray Irradiation on the Noise Behavior of Amorphous Indium-Gallium-Zinc-Oxide TFTs. Journal of the Electrochemical Society, 2020, 167, 027512.	1.3	4
382	Improvement of Hafnium Oxide Resistive Memory Performance Through Low-Temperature Supercritical Oxidation Treatments. IEEE Transactions on Electron Devices, 2021, 68, 541-544.	1.6	4
383	Impact of AC Stress in Low Temperature Polycrystalline Silicon Thin Film Transistors Produced With Different Excimer Laser Annealing Energies. IEEE Electron Device Letters, 2021, 42, 847-850.	2.2	4
384	Influences of aluminum doping on the microstructures and electrical properties of tantalum nitride thin films before and after annealing. Vacuum, 2022, 197, 110791.	1.6	4
385	A Functional Novel Logic for Max/Min Computing in One-Transistor-One-Resistor Devices With Resistive Random Access Memory (RRAM). IEEE Transactions on Electron Devices, 2022, 69, 1811-1815.	1.6	4
386	Formation of stacked nickel-silicide nanocrystals by using a co-mixed target for nonvolatile memory application. Surface and Coatings Technology, 2007, 202, 1292-1296.	2.2	3
387	Reduction of photoleakage current in polycrystalline silicon thin-film transistor using NH3 plasma treatment on buffer layer. Applied Physics Letters, 2008, 92, 153507.	1.5	3
388	Elimination of Photoleakage Current in Poly-Si TFTs Using a Metal-Shielding Structure. Electrochemical and Solid-State Letters, 2008, 11, J34.	2.2	3
389	Formation of NiSi2/SiN compound nanocrystal for nonvolatile memory application. Thin Solid Films, 2010, 518, 7324-7327.	0.8	3
390	Formation and composition of titanium oxinitride nanocrystals synthesized via nitridizing titanium oxide for nonvolatile memory applications. Thin Solid Films, 2011, 519, 7977-7981.	0.8	3
391	Dependence of Light-Accelerated Instability on Bias and Environment in Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistors. ECS Journal of Solid State Science and Technology, 2013, 2, Q74-Q76.	0.9	3
392	Abnormal threshold voltage shift under hot carrier stress in Ti1âˆ’xNx/HfO2 p-channel metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2013, 114, .	1.1	3
393	Electron-electron scattering-induced channel hot electron injection in nanoscale n-channel metal-oxide-semiconductor field-effect-transistors with high-k/metal gate stacks. Applied Physics Letters, 2014, 105, 143505.	1.5	3
394	Investigating degradation behavior of hole-trapping effect under static and dynamic gate-bias stress in a dual gate a-InGaZnO thin film transistor with etch stop layer. Thin Solid Films, 2016, 603, 359-362.	0.8	3
395	Investigating degradation behaviors induced by mobile Cu ions under high temperature negative bias stress in a-InGaZnO thin film transistors. Applied Physics Letters, 2017, 111, 133504.	1.5	3
396	Investigating degradation behaviors induced by hot carriers in the etch stop layer in amorphous InGaZnO thin film transistors with different electrode materials and structures. Thin Solid Films, 2017, 644, 45-51.	0.8	3

#	Article	IF	Citations
397	The Impact of Different TiN Capping Metal Thicknesses on High-k Oxygen Vacancies in n-MOSFETs. IEEE Transactions on Device and Materials Reliability, 2017, 17, 799-801.	1.5	3
398	Physical origin of the non-linearity in amorphous In-Ga-Zn-O thin-film transistor current-voltage characteristics. Solid-State Electronics, 2018, 147, 51-57.	0.8	3
399	A Study of Effects of Metal Gate Composition on Performance in Advanced n-MOSFETs. IEEE Transactions on Electron Devices, 2019, 66, 3286-3289.	1.6	3
400	Negative threshold voltage shift for LTPS TFTs under x-ray irradiation and gate bias. Semiconductor Science and Technology, 2019, 34, 095012.	1.0	3
401	Abnormal Positive Bias Temperature Instability Induced by Dipole Doped N-Type MOSCAP. IEEE Journal of the Electron Devices Society, 2019, 7, 897-901.	1.2	3
402	The Effect of Humidity on Reducing Forming Voltage in Conductive-Bridge Random Access Memory With an Alloy Electrode. IEEE Electron Device Letters, 2019, 40, 1606-1609.	2.2	3
403	A Novel Structural Design Serving as a Stress Relief Layer for Flexible LTPS TFTs. , 2019, , .		3
404	Abnormal ${C}$ â€“${V}$ Hump Effect Induced by Hot Carriers in Gate Length-Dependent p-Type LTPS TFTs. IEEE Transactions on Electron Devices, 2019, 66, 4764-4767.	1.6	3
405	Abnormal threshold voltage shift caused by trapped holes under hot-carrier stress in a-IGZO TFTs. Journal Physics D: Applied Physics, 2020, 53, 085104.	1.3	3
406	Influence of Hot Carriers and Illumination Stress on a-InGaZnO TFTs With Asymmetrical Geometry. IEEE Electron Device Letters, 2020, 41, 745-748.	2.2	3
407	The Relationship Between Resistive Protective Oxide (RPO) and Hot Carrier Stress (HCS) Degradation in n-Channel LD SOI MOSFET. IEEE Transactions on Electron Devices, 2021, 68, 962-967.	1.6	3
408	On the Optimization of Performance and Reliability in a-InGaZnO Thin-Film Transistors by Versatile Light Shielding Design. IEEE Transactions on Electron Devices, 2021, 68, 1654-1658.	1.6	3
409	Investigation of Degradation Behavior During Illuminated Negative Bias Temperature Stress in P-Channel Low-Temperature Polycrystalline Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2021, 42, 712-715.	2.2	3
410	Improved uniformity and threshold voltage in NbOx-ZrO2 selectors. Applied Physics Letters, 2021, 119, .	1.5	3
411	Performance Enhancement of InGaZnO Top-Gate Thin Film Transistor With Low-Temperature High-Pressure Fluorine Treatment. IEEE Electron Device Letters, 2021, 42, 1611-1614.	2.2	3
412	Dynamic switching-induced back-carrier-injection in a-InGaZnO thin film transistors. Journal Physics D: Applied Physics, 2021, 54, 025111.	1.3	3
413	Improvement of Strained Negative Bias Temperature Instability in Flexible LTPS TFTs by a Stress-Release Design. IEEE Transactions on Electron Devices, 2022, 69, 1532-1537.	1.6	3
414	Improving Reliability of a-InGaZnO TFTs With Optimal Location of Al₂O₃ Passivation in Moist Environment. IEEE Transactions on Electron Devices, 2022, 69, 3181-3185.	1.6	3

#	Article	IF	Citations
415	Analysis of abnormal threshold voltage shift induced by surface donor state in GaN HEMT on SiC substrate. Applied Physics Letters, 2022, 120, 233505.	1.5	3
416	Analysis of Meridian Flow Direction by Electrical Stimulation Method. Nanoscale Research Letters, 2022, 17, .	3.1	3
417	Variable Temperature Measurement on Operating Pentacene-Based OTFT. Materials Research Society Symposia Proceedings, 2008, 1091, 1.	0.1	2
418	Enhancement of NiSi-Based Nanocrystal Formation by Incorporating Ge Elements for Nonvolatile Memory Devices. Journal of the Electrochemical Society, 2009, 156, H751.	1.3	2
419	Effect of Lateral Body Terminal on Siliconâ€“Oxideâ€“Nitrideâ€“Oxideâ€“Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2011, 32, 1394-1396.	2.2	2
420	Low temperature synthesis and electrical characterization of germanium doped Ti-based nanocrystals for nonvolatile memory. Thin Solid Films, 2011, 520, 1136-1140.	0.8	2
421	Hot Carrier Effect on Gate-Induced Drain Leakage Current in n-MOSFETs with HfO2â^•Ti1-xNx Gate Stacks. Electrochemical and Solid-State Letters, 2012, 15, H211.	2.2	2
422	The Impact of Pre/Post-metal Deposition Annealing on Negative-Bias-Temperature Instability in HfO2 Stack p-Channel Metal-Oxide-Semiconductor Field Effect Transistors. ECS Solid State Letters, 2015, 4, Q37-Q39.	1.4	2
423	Trap state passivation improved hot-carrier instability by zirconium-doping in hafnium oxide in a nanoscale n-metal-oxide semiconductor-field effect transistors with high-k/metal gate. Applied Physics Letters, 2016, 108, 173504.	1.5	2
424	Impact of post-metal deposition annealing temperature on performance and reliability of high-K metal-gate n-FinFETs. Thin Solid Films, 2016, 620, 30-33.	0.8	2
425	Abnormal Recovery Phenomenon Induced by Hole Injection During Hot Carrier Degradation in SOI n-MOSFETs. IEEE Electron Device Letters, 2017, 38, 835-838.	2.2	2
426	Inert Pt electrode switching mechanism after controlled polarity-forming process in In2O3-based resistive random access memory. Applied Physics Express, 2017, 10, 094102.	1.1	2
427	Review of Recently Progress on Neural Electronics and Memcomputing Applications in Intrinsic SiOx-Based Resistive Switching Memory. , 2018, , .		2
428	Integrating a Charge Trapping Layer in Passivated Emitter Rear Contact Cell to Enhance Efficiency. IEEE Electron Device Letters, 2018, 39, 983-986.	2.2	2
429	Abnormal Unsaturated Output Characteristics In a-InGaZnO TFTs With Light Shielding Layer. IEEE Electron Device Letters, 2019, 40, 1281-1284.	2.2	2
430	Effect of a-InGaZnO TFT Channel Thickness under Self-Heating Stress. ECS Journal of Solid State Science and Technology, 2019, 8, Q185-Q188.	0.9	2
431	A characteristic improved technique and analysis with plasma treatment to the electrode on oxide-based resistive random access memory. Journal of Alloys and Compounds, 2020, 817, 150566.	2.8	2
432	Realization of Synapse Behaviors Based on Memristor and Simulation Study With KMC Method. IEEE Journal of the Electron Devices Society, 2020, 8, 981-985.	1.2	2

#	Article	IF	Citations
433	Analysis of increase in forward transconductance to determine the critical point of polarization at ferroelectric 1T1C memory. Applied Physics Letters, 2021, 118, .	1.5	2
434	Enhancing gate turn-off thyristor blocking characteristics by low temperature defect passivation technology. Semiconductor Science and Technology, 2021, 36, 085005.	1.0	2
435	Charge Carrier Mobility and Series Resistance Extraction in 2D Fieldâ€Effect Transistors: Toward the Universal Technique. Advanced Functional Materials, 2021, 31, 2105003.	7.8	2
436	Dynamic Behaviors and Training Effects in TiN/Ti/HfOx/TiN-Nanolayered Memristors with Controllable Quantized Conductance States: Implications for Quantum and Neuromorphic Computing Devices. ACS Applied Nano Materials, 2021, 4, 11296-11304.	2.4	2
437	Highly-Doped Region Optimization for Reduced Hot-Carrier Effects in Dual-Gate Low Temperature Polysilicon TFTs. IEEE Electron Device Letters, 2021, 42, 1794-1797.	2.2	2
438	Gate Dielectric Leakage Reduction in Hard-Mask Defined and Dry-Etch Patterned Organic TFTs Devices. IEEE Electron Device Letters, 2022, 43, 48-51.	2.2	2
439	Enhancing Reliability and 2 mm-Axial Mechanical Bending Endurance by Gate Insulator Improvements in Flexible Polycrystalline Silicon TFTs. IEEE Transactions on Electron Devices, 2022, 69, 2423-2429.	1.6	2
440	Improved diffusion and storage of lithium ions via recrystallization induced conducting pathways in a Li:Ta₂O₅-based electrolyte for all-solid-state electrochromic devices with enhanced performance. Nanotechnology, 2022, 33, 275711.	1.3	2
441	Physical Mechanism of the Mechanical Bending of High-Performance Organic TFTs and the Effect of Atmospheric Factors. ACS Applied Electronic Materials, 2022, 4, 3000-3009.	2.0	2
442	Investigation of the Self-Heating Effect in High Performance Organic TFTs With Multi-Finger Structure. IEEE Electron Device Letters, 2022, 43, 1243-1246.	2.2	2
443	Advanced supercritical fluid technique to reduce amorphous silicon defects in heterojunction solar cells. Semiconductor Science and Technology, 2022, 37, 085011.	1.0	2
444	Analysis of the buffer trap-induced kink effect in AlGaN/GaN HEMT on SiC substrate. Semiconductor Science and Technology, 0, , .	1.0	2
445	Abnormal Hump and Two-Step Degradation of Top Gate a-InGaZnO TFTs Under Positive Bias Stress. IEEE Transactions on Electron Devices, 2022, 69, 4288-4292.	1.6	2
446	P-17: High Performance Polycrystalline Silicon TFTs by Heat-Retaining Enhanced Crystallization for SOP and AMOLED Applications. Digest of Technical Papers SID International Symposium, 2006, 37, 246.	0.1	1
447	Formation of silicon germanium nitride layer with distributed charge storage elements. Applied Physics Letters, 2006, 88, 112105.	1.5	1
448	Reliability study on tri-gate nanowires poly-Si TFTs under DC and AC hot-carrier stress. , 2007, , .		1
449	13.3: A Novel aâ€Si TFT Pixel Circuit with High Immunity to the Degradation of the TFTs and OLEDs Used in AMOLED Displays. Digest of Technical Papers SID International Symposium, 2007, 38, 169-172.	0.1	1
450	Studies on nonvolatile resistance memory switching behaviors in InGaZnO thin films. , 2011, , .		1

#	Article	IF	Citations
451	N2O Plasma Treatment Suppressed Temperature-Dependent Point Defects Formation with Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistors. ECS Transactions, 2012, 45, 169-178.	0.3	1
452	Abnormal interface state generation under positive bias stress in TiN/HfO2 p-channel metal-oxide-semiconductor field effect transistors. Applied Physics Letters, 2012, 101, 133505.	1.5	1
453	Mechanical Stress Influence on Electronic Transport in Low-k SiOC Dielectric Dual Damascene Capacitor. IEEE Electron Device Letters, 2013, 34, 1056-1058.	2.2	1
454	N2O Plasma Treatment Suppressed Temperature-dependent Point Defects Formation with Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistors. ECS Transactions, 2013, 45, 47-55.	0.3	1
455	Investigation of defect-induced abnormal body current in fin field-effect-transistors. Applied Physics Letters, 2015, 107, 083503.	1.5	1
456	Pâ€8: Investigating the Degradation Behaviors for Bottom/Top Gate Sweep under Negative Bias Illumination Stress in Dual Gate InGaZnO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2015, 46, 1147-1150.	0.1	1
457	51.3: A Mobility Enhancing Method Adopting A Multiâ€Active Layer Structure in Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2015, 46, 772-774.	0.1	1
458	Effects of fabrication method on defects induced by nitrogen diffusion to the hafnium oxide layer in metalâ€“oxideâ€“semiconductor field effect transistors. Thin Solid Films, 2016, 620, 43-47.	0.8	1
459	Universal dependence on the channel conductivity of the competing weak localization and antilocalization in amorphous InGaZnO₄thin-film transistors. Applied Physics Express, 2017, 10, 051103.	1.1	1
460	A universal model for interface-type threshold switching phenomena by comprehensive study of Vanadium oxide-based selector. , 2017, , .		1
461	An Investigation of Anode Hole Injection-Induced Abnormal Body Current in n-Channel HfO₂/TiN MOSFETs. IEEE Journal of the Electron Devices Society, 2018, 6, 803-807.	1.2	1
462	Realization of Storage and Synaptic Simulation Behaviors Based on Different Forming Modes. IEEE Electron Device Letters, 2019, 40, 1257-1260.	2.2	1
463	Formation of Hump Effect Due to Top-Gate Bias Stress in Organic Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 1941-1944.	2.2	1
464	Interface Defect Shielding of Electron Trapping in a-InGaZnO Thin Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3645-3649.	1.6	1
465	Impact of Gate Size on Abnormal Current Rise Under an Electric Field in Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 1143-1148.	1.6	1
466	Oneâ€Selector Oneâ€Resistor Devices: Multiâ€Functional Controllable Memory Devices Applied for 3D Integration Based on a Single Niobium Oxide Layer (Adv. Electron. Mater. 1/2020). Advanced Electronic Materials, 2020, 6, 2070002.	2.6	1
467	The time response for the low-temperature poly-silicon thin-film transistors to x-ray irradiation pulse. Semiconductor Science and Technology, 2021, 36, 045003.	1.0	1
468	An Analytical Method for Parameter Extraction in Oxide Semiconductor Field-Effect Transistors. IEEE Transactions on Electron Devices, 2021, 68, 2717-2722.	1.6	1

#	Article	IF	Citations
469	Performance and Reliability Optimization of Supercritical-Nitridation-Treated AlGaN/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2021, 68, 4317-4321.	1.6	1
470	Investigation of degradation behavior under negative bias temperature stress in Si/Si_{0.8}Ge_{0.2} metal-oxide-semiconductor capacitors. Journal Physics D: Applied Physics, 2021, 54, 475103.	1.3	1
471	Analyzing the interface trap density in SiGe capacitors using an abnormal flat band voltage shift at low temperature. Applied Physics Express, 2020, 13, 111006.	1.1	1
472	Increasing Controllable Oxygen Ions to Improve Device Performance Using Supercritical Fluid Technique in ZnO-Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2022, 69, 127-132.	1.6	1
473	An Ultra Energy-Saving Metal/Insulator/Metal Structure for One Selector-One RRAM. , 2020, , .		1
474	Analysis of self-heating-related instability in n-channel low-temperature polysilicon TFTs with different S/D contact hole densities. Applied Physics Express, 2022, 15, 034003.	1.1	1
475	Investigating two-stage degradation of threshold voltage induced by off-state stress in AlGaN/GaN HEMTs. Semiconductor Science and Technology, 2022, 37, 025017.	1.0	1
476	Improving Drain-Induced Barrier Lowering Effect and Hot Carrier Reliability With Terminal via Structure on Half-Corbino Organic Thin-Film Transistors. IEEE Electron Device Letters, 2022, 43, 569-572.	2.2	1
477	Abnormal trend in hot carrier degradation with fin profile in short channel FinFET devices at 14 nm node. Semiconductor Science and Technology, 2022, 37, 045010.	1.0	1
478	Investigations on TaHf alloys for thin film resistor applications. Materials Chemistry and Physics, 2022, 285, 126027.	2.0	1
479	Analysis of Abnormal Current Rise Mechanism in GaN-MIS HEMT With Al₂O₃/Si₃N₄ Gate Insulator Under Hot Switching. IEEE Transactions on Electron Devices, 2022, 69, 4218-4223.	1.6	1
480	P-2: A Novel Self-Aligned SiGe Elevated S/D polycrystalline-Silicon Thin-Film Transistor. Digest of Technical Papers SID International Symposium, 2002, 33, 204.	0.1	0
481	P-15: Highly Reliable Amorphous Si TFT with Low Leakage for AMLCD and AMOLED Applications. Digest of Technical Papers SID International Symposium, 2005, 36, 280.	0.1	0
482	P-12: Mobility Enhancement of Pattern-dependent Metal-Induced Lateral Crystallization Polysilicon Thin-Film Transistors with Different Dimensions. Digest of Technical Papers SID International Symposium, 2005, 36, 268.	0.1	0
483	High-performance polycrystalline silicon thin-film transistors with oxideâ€“nitrideâ€“oxide gate dielectric and multiple nanowire channels. Thin Solid Films, 2006, 515, 1112-1116.	0.8	0
484	Formation of the distributed NiSiGe nanocrystals nonvolatile memory formed by rapidly annealing in N2 and O2 ambient. Thin Solid Films, 2010, 518, 7304-7307.	0.8	0
485	Investigation of resistive switching properties in Sm<inf>2</inf>O<inf>3</inf> memory devices. , 2011, , .		0
486	Impact of strain on gate-induced floating body effect for partially depleted silicon-on-insulator p-type metalâ€“oxideâ€“semiconductor-field-effect-transistors. Thin Solid Films, 2013, 528, 10-18.	0.8	0

#	Article	IF	Citations
487	Investigating bipolar resistive switching characteristics in filament type and interface type BON-based resistive switching memory. Thin Solid Films, 2013, 529, 389-393.	0.8	0
488	Anomalous Gate Current Hump after Dynamic Negative Bias Stress and Negative-Bias Temperature-Instability in p-MOSFETs with HfxZr1â^'xO2and HfO2/Metal Gate Stacks. ECS Journal of Solid State Science and Technology, 2013, 2, Q187-Q191.	0.9	0
489	P.15: Influence of Photoâ€Thermal Preâ€treatment on Electrical Characteristics and Reliability of Znâ€Snâ€O Thinâ€Film Transistors. Digest of Technical Papers SID International Symposium, 2013, 44, 1037-1039.	0.1	0
490	Influence of nitrogen buffering on oxygen in indium-tin-oxide capped resistive random access memory with NH3 treatment. , 2015, , .		0
491	A synaptic device built in one diodeâ€“one resistor (1Dâ€“1R) architecture with intrinsic SiOx-based resistive switching memory. ChemistrySelect, 2016, 1, .	0.7	0
492	P-18: High Reliability Amorphous-Oxide Thin-Film Transistors with an Expanded-Electrode Structure. Digest of Technical Papers SID International Symposium, 2016, 47, 1183-1185.	0.1	0
493	Investigating non-filament type conduction mechanism of indium-tin-oxide resistance random access memory by varying forming current compliance. , 2016, , .		0
494	Identical off-state current raise induced by photo-induced schottky barrier lowering in a-InGaZnO<inf>4</inf> thin film transistors. , 2016, , .		0
495	Investigation of abnormal off-current in p-channel double diffused drain metal-oxide-semiconductor transistors after hot carrier stress. , 2016, , .		0
496	Resistive Random Access Memory: Solving the Scaling Issue of Increasing Forming Voltage in Resistive Random Access Memory Using Highâ€k Spacer Structure (Adv. Electron. Mater. 9/2017). Advanced Electronic Materials, 2017, 3, .	2.6	0
497	Organometal tri-halide perovskite resistive switching device with PMMA electrode interlayer. , 2017, , .		0
498	Implementation of Functionally Complete Boolean Logic and 8-Bit Adder in CMOS Compatible 1T1R RRAMs for In-Memory Computing. , 2018, , .		0
499	16â€3: Investigation of Mechanical Stress and Gate Bias Stress on Flexible Dualâ€gate aâ€IGZO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2019, 50, 214-216.	0.1	0
500	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at R=2mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. IEEE Electron Device Letters, 2019, , 1-1.	2.2	0
501	Abnormal Back Channel Leakage Under Large Drain Voltage in Short Channel Organic Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 1752-1755.	2.2	0
502	Predicting voltage induced positive-feedback effect on dynamic reset behavior in resistance switching device. Journal Physics D: Applied Physics, 2019, 52, 095108.	1.3	0
503	Reliability enhancement in dipole-doped metal oxide semiconductor capacitor induced by low-temperature and high-pressure nitridation. Applied Physics Express, 2021, 14, 034002.	1.1	0
504	Abnormal hump in low temperature in SiGe devices with silicon capping insertion layer. Journal Physics D: Applied Physics, 2021, 54, 415105.	1.3	0

#	Article	IF	Citations
505	Clarifying the switching layer transformation through analysis of an abnormal Iâ€“V curves with increasing set compliance current in oxide-based resistive random access memory. Applied Physics Express, 2021, 14, 094007.	1.1	0
506	Vertical Electric Field-Induced Abnormal Capacitanceâ€“Voltage Electrical Characteristics in a-InGaZnO TFTs. IEEE Transactions on Electron Devices, 2021, 68, 4431-4436.	1.6	0
507	Corrections to â€œTotal-Dose Effect of X-ray Irradiation on Low-TemperaturePolycrystalline Silicon Thin-Film Transistorsâ€•[Jun 20 864-867]. IEEE Electron Device Letters, 2020, 41, 1448-1448.	2.2	0
508	Investigation of degradation mechanism after negative bias temperature stress in Si/SiGe channel metal-oxide-semiconductor capacitors induced by hydrogen diffusion. Semiconductor Science and Technology, 0, , .	1.0	0
509	Design for Enhancing the Performance of Memristive Convolution Neural Network. , 2020, , .		0
510	Effects of X-ray accelerating voltage on electrical properties and reliability for ferroelectric random-access memory (FeRAM). Applied Physics Express, 2022, 15, 034002.	1.1	0
511	Suppressing Drain-Induced Barrier Lowering and Kink Effect in Low-Temperature Poly-Si TFTs Using a Partitioned Light Shield. IEEE Electron Device Letters, 2022, 43, 576-579.	2.2	0
512	A Method to Measure Polarization Signal of Nanoscale One-Transistor-One-Capacitor Ferroelectric Memory. IEEE Electron Device Letters, 2022, 43, 862-865.	2.2	0